



YJQ4D8G04H

N-Channel Enhancement Mode Field Effect Transistor

Product Summary

| | |
|----------------------------------|------|
| V_{DS} | 40V |
| I_D | 75A |
| $R_{DS(ON)}$ (at $V_{GS}=10V$) | 4.8m |
| 100% EAS Tested | |
| 100% V_{DS} Tested | |

General Description

Excellent package for heat dissipation
High density cell design for low $R_{DS(ON)}$



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Electrical Characteristics ($T_J=25$ unless otherwise noted)

| Parameter | Symbol | Conditions | Min | Typ | Max | Units |
|---------------------------------|------------|----------------------------------|-----|-----|-----|-------|
| Static Parameter | | | | | | |
| Drain-Source Breakdown Voltage | BV_{DSS} | $V_{GS}=0V, I_D$ | 40 | - | - | V |
| | | $V_{GS}=0V, I_D=1mA$ | 40 | - | - | V |
| Zero Gate Voltage Drain Current | I_{DSS} | $V_{DS}=40V, V_{GS}=0V$ | - | - | 1 | |
| | | $V_{DS}=40V, V_{GS}=0V, T_J=125$ | - | - | 100 | |

Gate-Body Leakage Current



Typical Electrical and Thermal Characteristics Diagrams

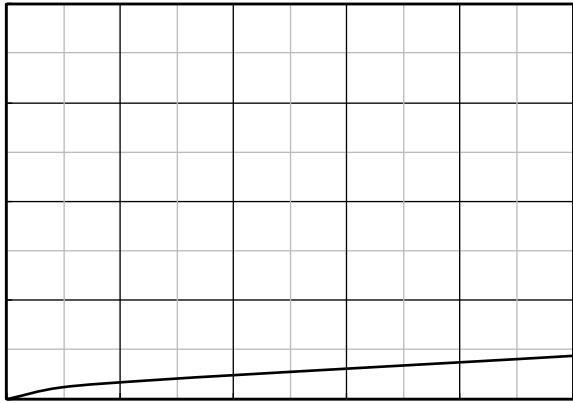


Figure 1. Output Characteristics

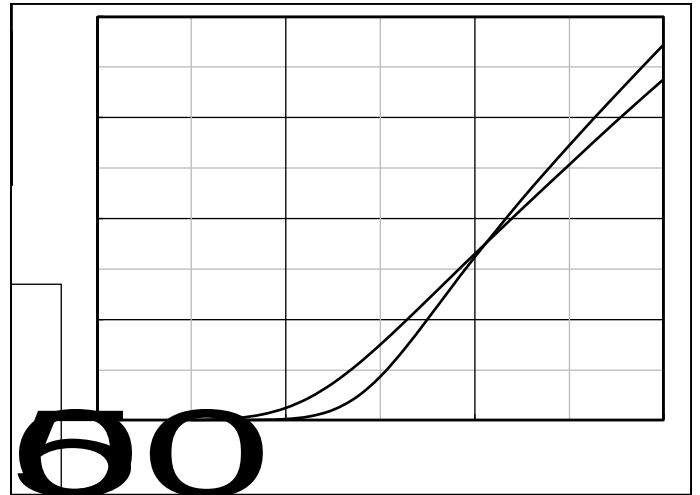


Figure 2. Transfer Characteristics

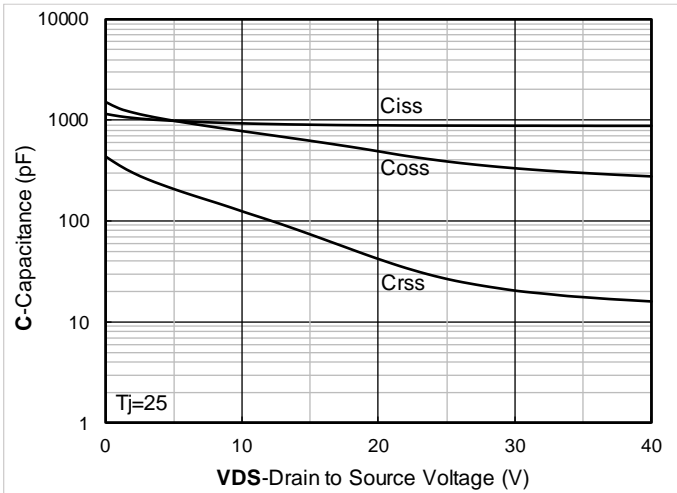


Figure 3. Capacitance Characteristics

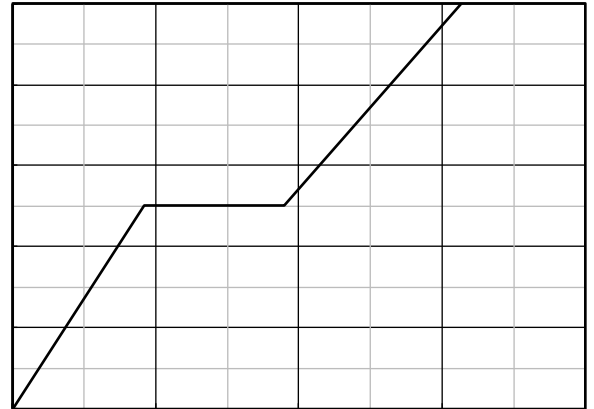


Figure 4. Gate Charge

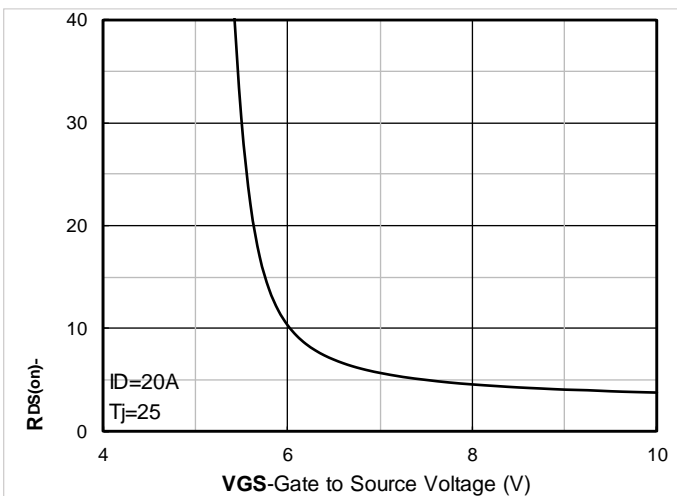


Figure 5. On-Resistance vs Gate to Source Voltage

Figure 6. Normalized On-Resistance



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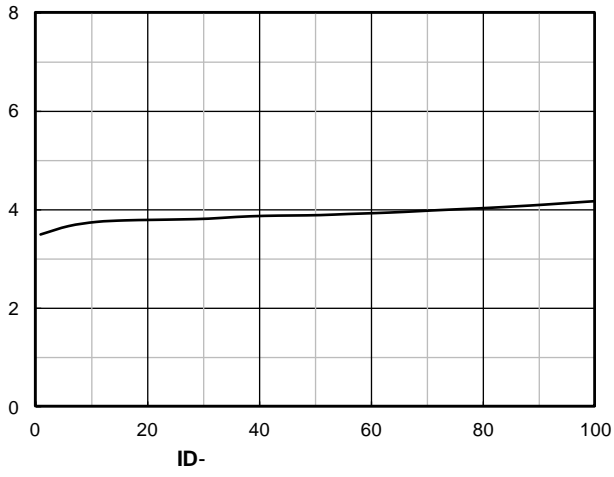
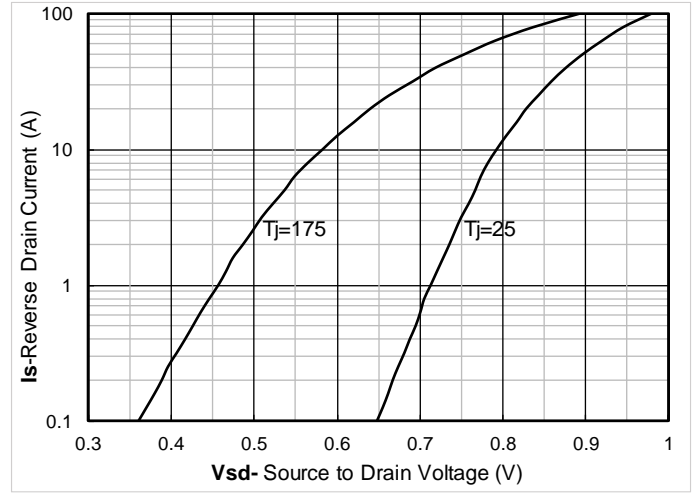


Figure 7. $R_{DS(on)}$





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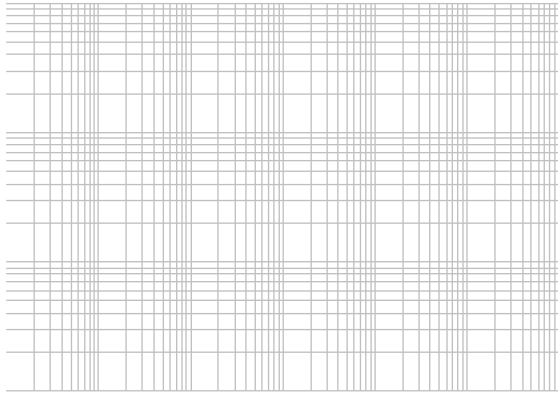


Figure 13. Maximum Transient Thermal Impedance

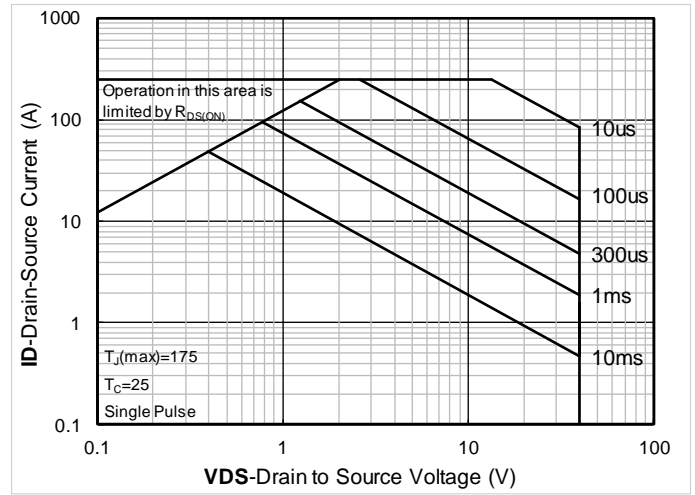


Figure 14. Safe Operation Area

Test Circuits & Waveforms



Figure A. Unclamped Inductive Switching (UIS) Test Circuit & Waveform



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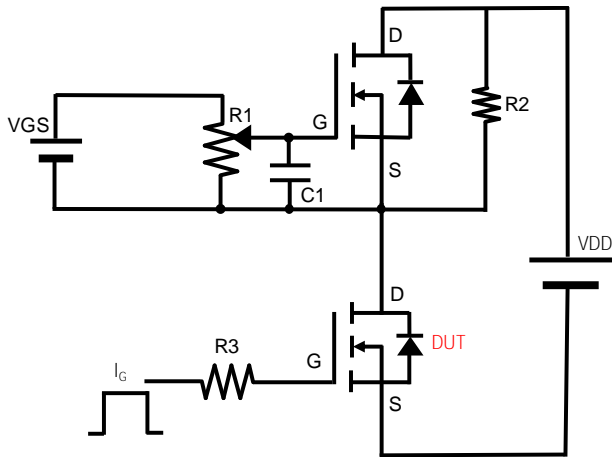


Figure B. Gate Charge Test Circuit & Waveform

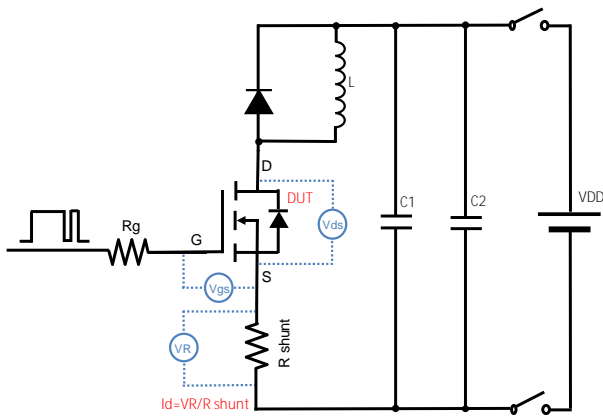


Figure C. Resistive Switching Test Circuit & Waveform

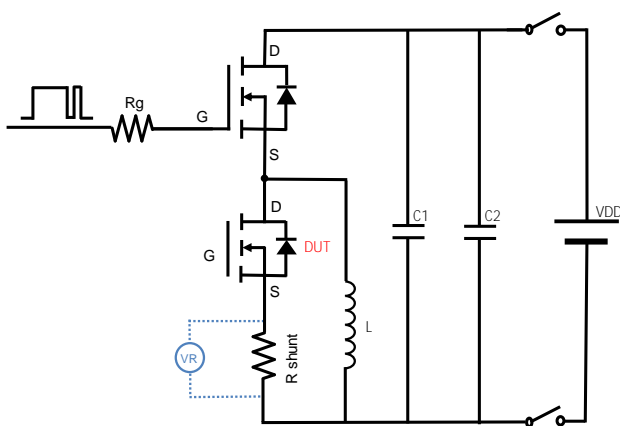
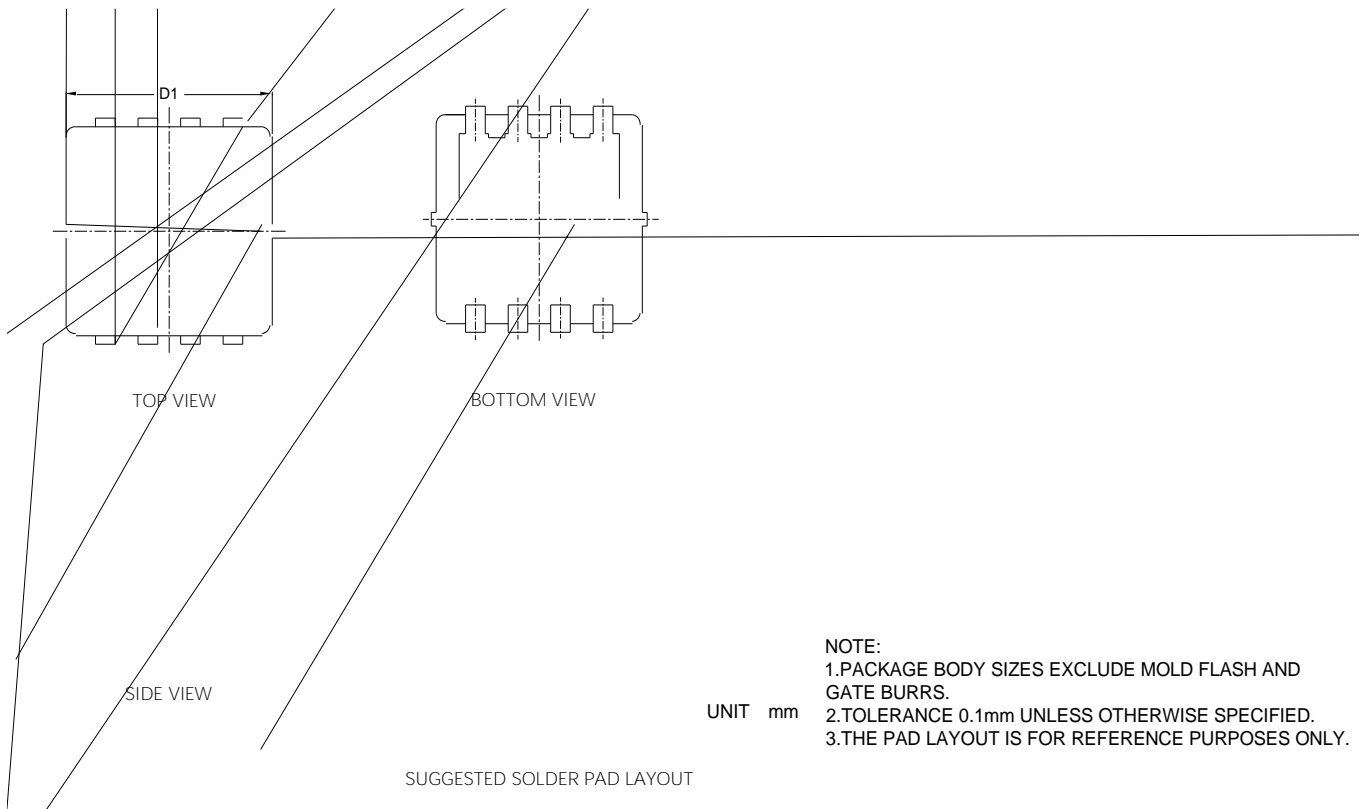


Figure D. Diode Recovery Test Circuit & Waveform



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PDFN3333-8L-B-0.75MM Package information



- NOTE:
- 1.PACKAGE BODY SIZES EXCLUDE MOLD FLASH AND GATE BURRS.
 - 2.TOLERANCE 0.1mm UNLESS OTHERWISE SPECIFIED.
 - 3.THE PAD LAYOUT IS FOR REFERENCE PURPOSES ONLY.

UNIT mm



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